

GSDBAV99

Monolithic Dual Switching Diode Common Anode

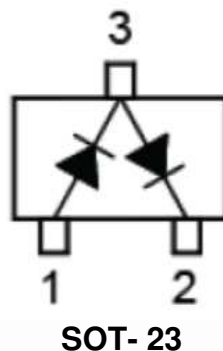
Product Description

Switching Diode 200mA / 70V

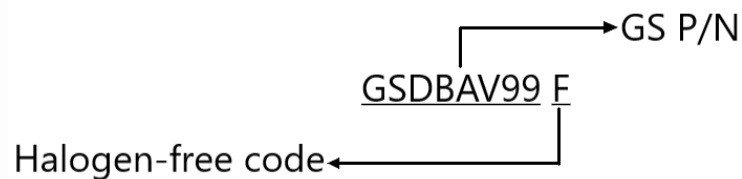
Features

- Low forward voltage
- For high-speed switching applications
- Halogen-free parts

Packages



Ordering Information



Part Number	Package	Quantity
GSDBAV99F	SOT- 23	3000 PCS

Marking Information

Part Number	Package	Part Marking
GSDBAV99F	SOT- 23	A7

Maximum Ratings

(T_A=25°C Unless otherwise noted)

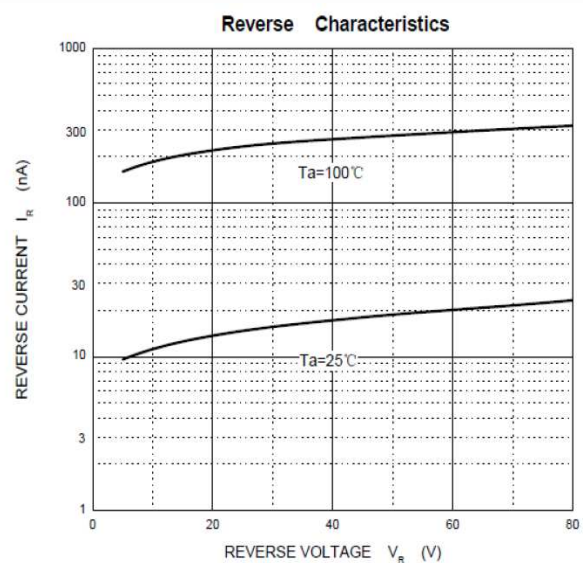
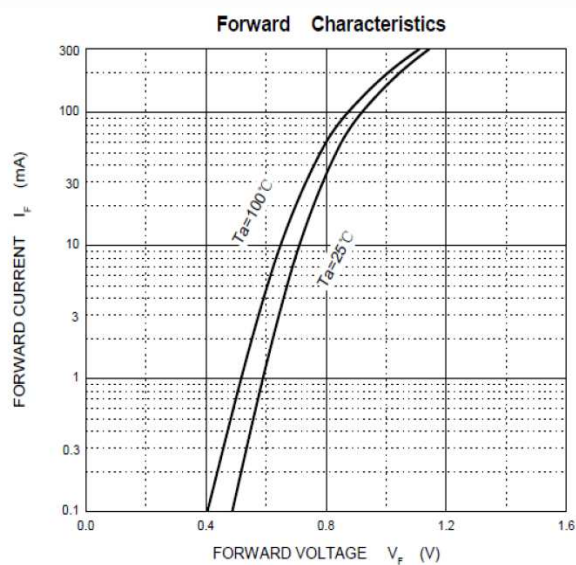
Symbol	Conditions	Value	Unit
V _R	Reverse Voltage	70	V
I _F	Forward Current	200	mA
P _D	Total Power Dissipation	225	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C

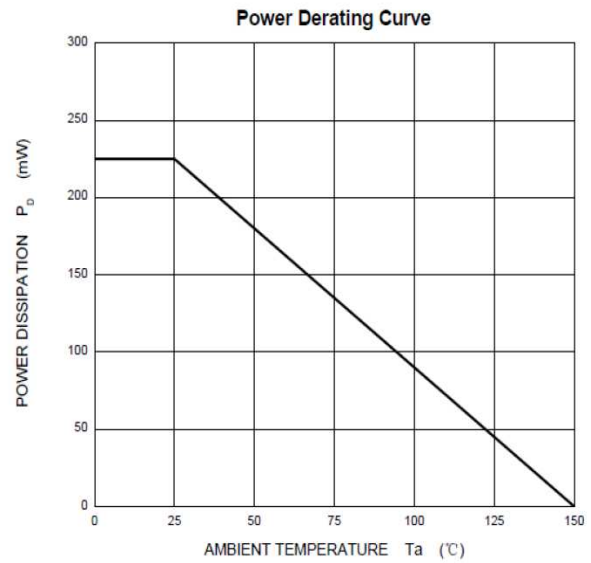
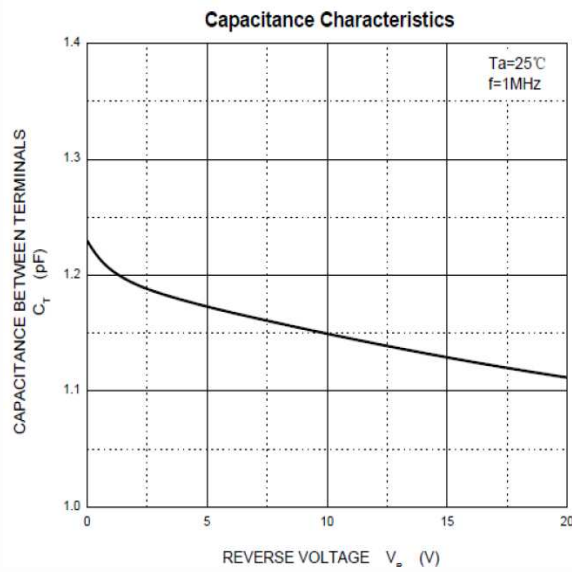
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

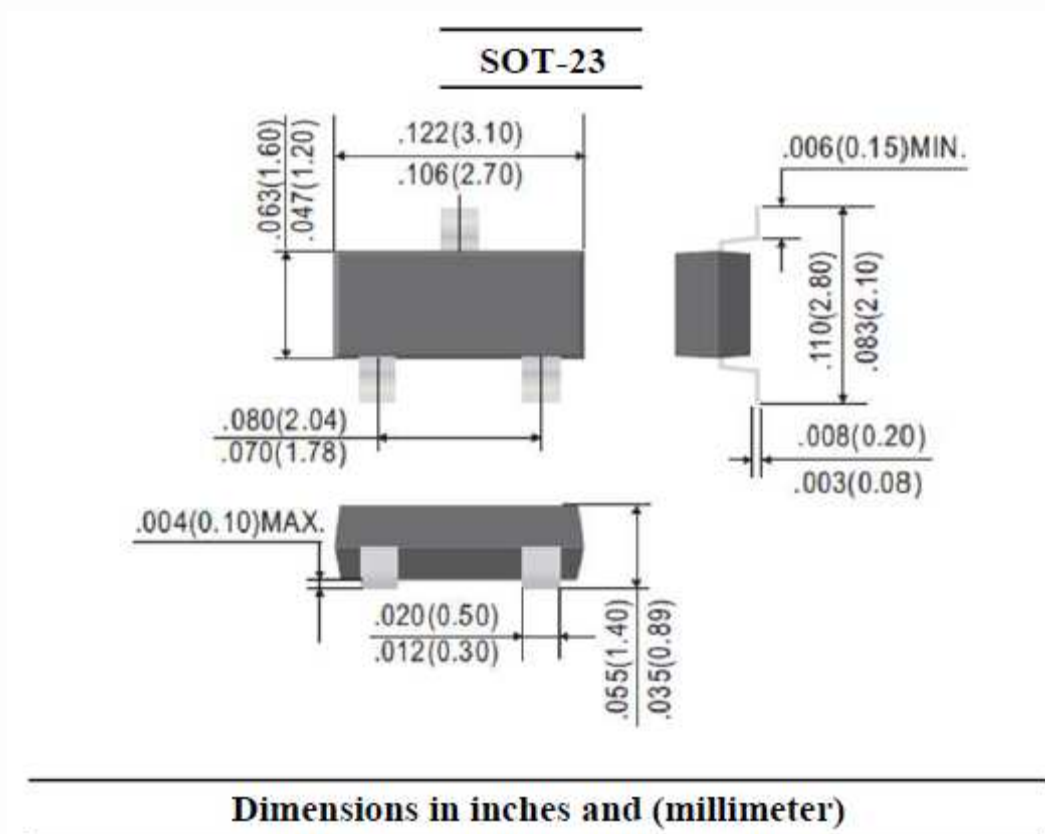
Symbol	Conditions	Max	Unit
V _F	Forward Voltage (I _F =1.0mA) (I _F =10mA) (I _F =50mA) (I _F =150mA)	715 855 1000 1250	mV
I _R	Reverse Current , V _R =70V	2.5	μA
C _d	Diode Capacitance (V _R =0V, f=1.0MHz),	1.5	pF
T _{rr}	Reverse Recovery Time I _F =I _R =10mA I _{rr} =0.1 * I _R , R _L =100Ω	6	ns

Typical Characteristics





Package Dimension



NOTICE

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